

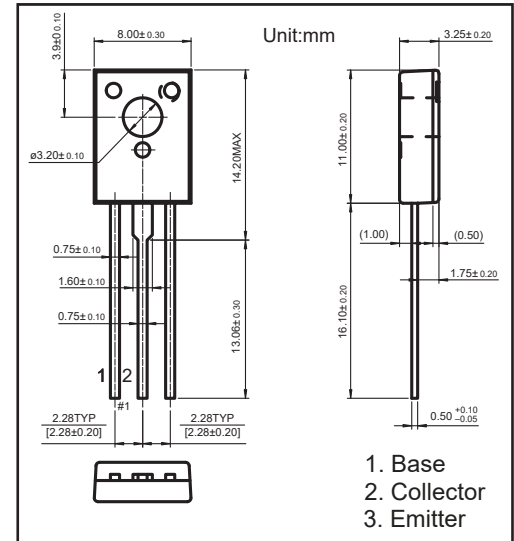
TO-18 Plastic-Encapsulate Transistors

FEATURES

- Low Frequency Power Amplifier
- Collector-Emitter Voltage :-160V
- Current :-1.5A
- PNP Transistor

MECHANICAL DATA

- Case style:TO-18 molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector- Base Voltage	V_{CBO}	-180	V
Collector-Emitter Voltage	V_{CEO}	-160	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current -Continuous	I_C	-1.5	A
Collector Dissipation	P_C	1	W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{stg}	-55-150	°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -1mA, I_E = 0$	-180			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10mA, I_B = 0$	-160			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -1mA, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -160V, I_E = 0$			-10	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4V, I_C = 0$			-10	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -5V, I_C = -150mA$	60		200	
	$h_{FE(2)}$	$V_{CE} = -5V, I_C = -500mA$	30			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500mA, I_B = -50mA$			-1	V
Base-emitter voltage	V_{BE}	$V_{CE} = -5V, I_C = -150mA$			-1.5	V
Transition frequency	f_T	$V_{CE} = -5V, I_C = -150mA$		140		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$		27		pF